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COMPOSITE SEMICONDUCTOR DEVICE

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[There are no amendments to this patent.]

Claims

1. A composite semiconductor device characterized by the fact that a first semiconductor device having a bipolar element and a second semiconductor device having an operating layer composed of a compound semiconductor are arranged so that they face each other; and that in wiring of said first semiconductor device and the wiring of said second semiconductor device are connected by a melt with a low melting point.

2. The composite semiconductor device of Claim 1 characterized by the fact that the wiring of the above-mentioned first semiconductor device and an electrode of the above-mentioned second semiconductor device, or an electrode of the above-mentioned first semiconductor device and the wiring of the above-mentioned second semiconductor device, are connected by a melt with a low melting point.

3. The composite semiconductor device of Claims 1 and 2, characterized by the fact that the above-mentioned second semiconductor device includes several semiconductor devices.

4. The composite semiconductor device of Claims 1, 2, and 3, characterized by the fact that the above-mentioned second semiconductor device has an active layer composed of a compound semiconductor.

5. The composite semiconductor device of Claims 1, 2, 3, and 4, characterized by the fact that the above-mentioned first semiconductor device is a silicon wafer in which several semiconductor devices are assembled.

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